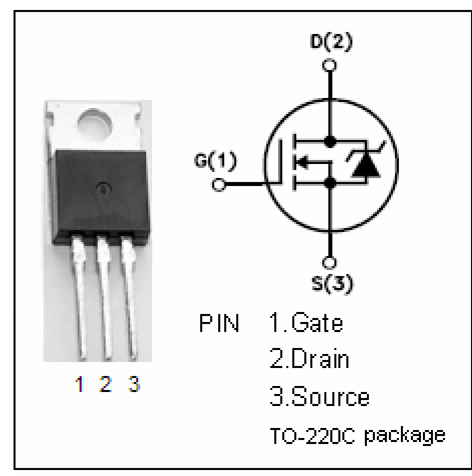
isc N-Channel MOSFET Transistor IRF630B



DESCRIPTION

- Drain Current $-I_D$= 9A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 200V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ = 0.4Ω(Max)
- Fast Switching Speed



APPLICATIONS

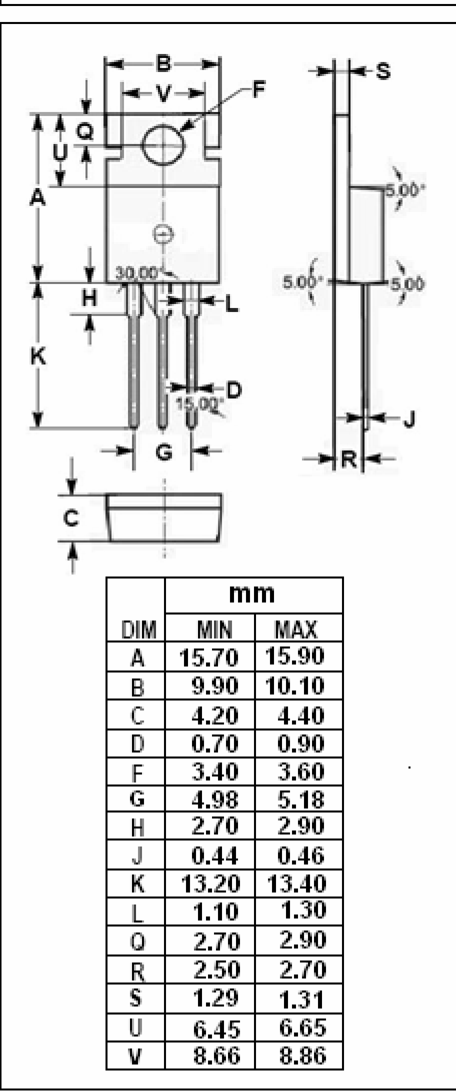
- Desinged for high efficiency switching DC/DC converters, switch mode power supplies, DC-AC converters for unin-terrupted power supply and motor control applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	200	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-continuous@ T_C=25℃	9	A
P_D	Power Dissipation@T_C=25℃	72	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.74	℃/W
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	62.5	℃/W



DIM	mm MIN	mm MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

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• ELECTRICAL CHARACTERISTICS (T_C=25℃)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 0.25mA	200		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 0.25mA	2	4	V
$R_{DS(on)}$	Drain-Source On-stage Resistance	V_{GS}= 10V; I_D= 4.5A		0.4	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±30V; V_{DS}= 0		±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 200V; V_{GS}= 0		10	uA
V_{SD}	Diode Forward Voltage	I_F= 9A; V_{GS}= 0		1.5	V